Microwave Resistance of Gallium Arsenide and Silicon p-i-n Diodes

R.H. Caverly and G. Hiller. "Microwave Resistance of Gallium Arsenide and Silicon p-i-n Diodes." 1987 MTT-S International Microwave Symposium Digest 87.2 (1987 Vol. II [MWSYM]): 591-594.

The purpose of this paper is to demonstrate that the p-i-n diode resistance is definable as a function of frequency and depends on the diode geometry and electronic properties. A formula for the p-i-n diode resistance is presented and compared with experimental resistance versus frequency data for both silicon and gallium arsenide p-i-n diodes.

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